

B1
a low reflection film coated on a second end of the multi-layer film opposite to the first end and comprising essentially Al_2O_3 having a resistivity of $1 \times 10^{12} \Omega\cdot\text{m}$ or more.

8. (Amended) A semiconductor laser device comprising:

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a semiconductor multi-layer film formed by laminating optical confinement layers and active layers so as to dispose each of said active layers between said optical confinement layers;

a high reflection film coated on a first end of the multi-layer film perpendicular to junction planes of the individual layers in said semiconductor multi-layer film; and

a low reflection film coated on a second end of the multilayer film opposite to the first end and comprising essentially Al_2O_3 having a stoichiometric ratio composition.

18. (Amended) A semiconductor laser device comprising:

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a semiconductor multi-layer film comprising at least one confinement layer and at least one active layer;

a high reflection film substantially perpendicular to the semiconductor multi-layer film; and

a low reflection film substantially perpendicular to the semiconductor multi-layer film, wherein the low reflection film comprises essentially Al_2O_3 having a stoichiometric ratio composition.

Please add Claim 20 as follows:

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20. (New) A semiconductor laser device comprising: